NSN 5962-01-376-1162

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-376-1162

Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
5975-01-253-6144 junction box
Features Provided:
Bidirectional and bipolar and high impedance and w/enable and w/disable and electrostatic sensitive and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
180.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 printed circuit
Shelf Life:

N/a

NSN 5962-01-376-1162

Memory Microcircuit - Page 2 of 2



Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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